a conduction structure configured to conduct static electricity generated on the worktable to a grounded portion outside the process chamber, the conduction structure having a conduction route for the static electricity including a conductive film formed on the worktable, formed on the pedestal, and electrically isolated from the casing of the chamber,

C1 wherein the conductive film is integrally formed and made of a same material as on the worktable and the pedestal.

35. (Amended) A single-substrate-processing apparatus, comprising:

an airtight process chamber including a casing and configured to process a target substrate;

a worktable configured to support the target substrate within the casing of the process chamber,

C2 a pedestal connected to the worktable to support the worktable; and

a conduction structure configured to conduct static electricity generated on the worktable to a grounded portion outside the process chamber, the conduction structure having a conduction route for the static electricity including a conductive film formed on the worktable and the pedestal, the conduction structure being arranged such that the conductive film and a conductive portion of the casing are electrically connected to ground,

wherein the conductive film is integrally formed and made of a same material as on the worktable and the pedestal.

Please add the following new Claims 40-48:

40. (New) The apparatus according to claim 21, further comprising:

a bias section configured toy apply an electrical potential to the conduction structure.

C3 41. (New) The apparatus according to claim 21, wherein the worktable and the pedestal are made of a ceramic.

42. (New) The apparatus according to claim 41, further comprising:

a bias section configured to apply an electrical potential to the conduction structure.

43. (New) The apparatus according to claim 35, wherein the worktable and the pedestal are made of a ceramic.

44. (New) The apparatus according to claim 43, further comprising:

a bias section configured to apply an electrical potential to the conduction structure.

45. (New) A single-substrate-processing apparatus for performing a semiconductor process, comprising:

a process chamber including a casing and configured to process a target substrate;

a ceramic worktable configured to support the target substrate within the casing,

a ceramic pedestal standing upright in the casing and connected to the worktable to support the worktable;

a conductive film integrally formed and made of a same material as on the worktable and the pedestal and covering the worktable and the pedestal, the conductive film being electrically connected to a conductive portion outside the casing while being electrically isolated from the casing; and

a bias section configured to apply an electrical potential to the conductive portion.

46. (New) The apparatus according to claim 45, wherein the conductive film comprises at least one of silicon carbide and titanium oxide.

47. (New) The apparatus according to claim 45, wherein the conductive film has a thickness from 20 to 100 μm.

48. (New) The apparatus according to claim 45, further comprising: